# 32-Channel, 14-Bit DAC with Full-Scale Output <br> Voltage Programmable from 50 V to 200 V 

## FEATURES

- High integration
- 32-channel, 14-bit denseDAC® with integrated high voltage output amplifier
- Guaranteed monotonic
- Housed in a $15 \mathrm{~mm} \times 15 \mathrm{~mm}$ CSP_BGA package
- Full-scale output voltage programmable from 50 V to 200 V through reference input
- 150/40 $\mu \mathrm{A}$ source/sink drive capability
- Integrated silicon diode for temperature monitoring
- SPI
- 1.2 MHz channel update rate
- Asynchronous RESET facility
- $-10^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ temperature range


## FUNCTIONAL BLOCK DIAGRAM



Figure 1. Functional Block Diagram

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## REVISION HISTORY

2/2024—Rev. 0 to Rev. A
Changes to Input High Voltage Parameter, Table 1 ..... 3
10/2023—Revision 0: Initial Version

## SPECIFICATIONS

$\mathrm{V}_{\mathrm{PP}}=55 \mathrm{~V}$ to $225 \mathrm{~V}, 4.75 \leq \mathrm{V}_{+} \leq 5.25 \mathrm{~V}, 4.75 \mathrm{~V} \leq \mathrm{AV}_{C C} \leq 5.25 \mathrm{~V}, 2.7 \mathrm{~V} \leq \mathrm{DV} \mathrm{C}_{\mathrm{CC}} \leq 5.25 \mathrm{~V}, \mathrm{PGND}=\mathrm{AGND}=\mathrm{DGND}=\mathrm{DAC} G N D=0 \mathrm{~V}, \mathrm{AV}_{C C}$ and $\mathrm{V}_{+}$must exceed REF_N by 1.15 V minimum, $1 \mathrm{~V} \leq$ REF_IN $\leq 4.096 \mathrm{~V},-10^{\circ} \mathrm{C} \leq \mathrm{T}_{\mathrm{A}} \leq+85^{\circ} \mathrm{C}$, unless otherwise noted.

Table 1. Specifications

| Parameter ${ }^{1}$ | Min | Typ | Max | Unit | Test Conditions/Comments |
| :---: | :---: | :---: | :---: | :---: | :---: |
| DC PERFORMANCE ${ }^{2,3}$ |  |  |  |  |  |
| Resolution |  | 14 |  | Bits |  |
| Integral Nonlinearity (INL) |  | $\pm 0.1$ |  | \% of full-scale range (FSR) |  |
| Differential Nonlinearity (DNL) | -1 |  | +1 | LSB | Guaranteed monotonic |
| Zero Code Voltage |  |  | +1 |  |  |
| Output Offset Error | -1 |  | +1 | V |  |
| Offset Drift |  | 0.5 |  | $\mathrm{mV} /{ }^{\circ} \mathrm{C}$ |  |
| Voltage Gain | 49 | 50 | 51 | V/V | Per channel |
| Gain Temperature Coefficient |  | -20 |  | ppm/ $/{ }^{\circ} \mathrm{C}$ |  |
| OUTPUT CHARACTERISTICS |  |  |  |  |  |
| Output Voltage Range ${ }^{2}$ |  |  |  |  |  |
| No Load | 1 |  | $V_{\text {PP }}-1.5$ | V |  |
| 4 M 2 Load to Ground (GND) | 1 |  | $V_{P P}-2.5$ | V |  |
| Output Impedance |  | 50 |  | $\Omega$ |  |
| Resistive Load ${ }^{4}$ | 4 |  |  | M $\Omega$ | To GND |
| Capacitive Load |  |  | 200 | pF |  |
| Short-Circuit Current ${ }^{5}$ |  |  |  |  |  |
| Sourcing |  | 0.15 |  | mA |  |
| Sinking |  | 0.04 |  | mA |  |
| DC Crosstalk | -4 |  | +4 | LSB |  |
| DC Power Supply Rejection Ratio (PSRR), VPP |  | -70 |  | dB |  |
| Long-Term Drift |  | 0.25 |  | LSB | Outputs at midscale, measured over 30 days at $25^{\circ} \mathrm{C}$ |
| AC CHARACTERISTICS |  |  |  |  |  |
| Settling Time |  |  |  |  |  |
| Falling Edge |  |  |  |  |  |
| $3 / 4$ to $1 / 4$ Scale Step |  | 70 |  | $\mu \mathrm{s}$ | No load |
|  |  | 470 |  | $\mu \mathrm{s}$ | 200 pF load |
| 1 LSB Step |  | 20 |  | $\mu \mathrm{s}$ |  |
| Rising Edge |  |  |  |  |  |
| $1 / 4$ to $3 / 4$ Scale Step |  | 70 |  | $\mu \mathrm{s}$ | No load |
|  |  | 190 |  | $\mu \mathrm{S}$ | 200 pF load |
| 1 LSB Step |  | 10 |  | $\mu \mathrm{s}$ |  |
| Slew Rate |  |  |  |  |  |
| Falling Edge |  | 1.2 |  | V/us | No load |
|  |  | 0.2 |  | V/ $/ \mathrm{s}$ | 200 pF load |
| Rising Edge |  | 1.6 |  | V/us | No load |
|  |  | 0.6 |  | V/ $/ \mathrm{s}$ | 200 pF load |
| -3 dB Bandwidth | 30 |  |  | kHz |  |
| Output Noise Spectral Density |  | 4.5 |  | $\mu \mathrm{V} / \mathrm{VHz}$ | Measured at 10 kHz |
| 0.1 Hz to 10 Hz Output Noise Voltage |  | 1 |  | mVp-p |  |
| Digital-to-Analog Glitch Impulse |  |  |  |  | 1 LSB change around major carry |
| Positive Transition |  | 15 |  | nV-sec |  |
| Negative Transition |  | 8 |  | nV -sec |  |
| Analog Crosstalk |  | 1 |  | $\mu \mathrm{V}$-sec |  |

## SPECIFICATIONS

Table 1. Specifications (Continued)

| Parameter ${ }^{1}$ | Min | Typ | Max | Unit | Test Conditions/Comments |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Digital Feedthrough |  | 2 |  | nV-sec |  |
| VOLTAGE REFERENCE, REF_IN ${ }^{6}$ <br> Input Voltage Range <br> Input Impedance | 1 |  | $\begin{aligned} & 4.096 \\ & 60 \end{aligned}$ | $\begin{aligned} & \mathrm{V} \\ & \mathrm{k} \Omega \end{aligned}$ |  |
| TEMPERATURE MEASUREMENT DIODE <br> Peak Inverse Voltage ( $\mathrm{P}_{\mathrm{IV}}$ ) <br> Forward Diode Drop, Forward Voltage $\left(V_{F}\right)$ <br> Forward Diode Current, Forward Current $\left(I_{F}\right)$ <br> $V_{F}$ Temperature Coefficient ( $T_{C}$ ) |  | $\begin{aligned} & 0.65 \\ & -2.20 \end{aligned}$ | $\begin{aligned} & 5 \\ & 0.8 \\ & 150 \end{aligned}$ | V <br> V <br> $\mu \mathrm{A}$ <br> $\mathrm{mV} /{ }^{\circ} \mathrm{C}$ | Cathode to anode $\mathrm{I}_{\mathrm{F}}=100 \mu \mathrm{~A}$, anode to cathode Anode to cathode Anode to cathode |
| DIGITAL INPUTS <br> Input Current <br> Input Low Voltage <br> Input High Voltage <br> Input Hysteresis (SCLK and SYNC Only) Input Capacitance | $\begin{aligned} & 0.8 \times \mathrm{DV}_{\mathrm{CC}} \\ & 2 \end{aligned}$ | $\pm 5$ <br> 200 | $\begin{aligned} & \pm 10 \\ & 0.2 \times \mathrm{DV}_{\mathrm{CC}} \end{aligned}$ $10$ | $\mu \mathrm{A}$ <br> V <br> V <br> V <br> mV <br> pF | $\begin{aligned} & -10^{\circ} \mathrm{C} \leq \mathrm{T}_{\mathrm{A}} \leq 85^{\circ} \mathrm{C} \\ & -10^{\circ} \mathrm{C} \leq \mathrm{T}_{\mathrm{A}} \leq 80^{\circ} \mathrm{C} \end{aligned}$ |
| POWER SUPPLY VOLTAGES $\begin{aligned} & \mathrm{V}_{\mathrm{PP}} \\ & \mathrm{~V}_{+} \\ & \mathrm{AV}_{\mathrm{CC}} \\ & \mathrm{DV} \mathrm{CD} \end{aligned}$ | $\begin{array}{\|l} (51 \times \text { REF_IN })+2.5 \\ 4.75 \\ 4.75 \\ 2.7 \end{array}$ |  | $\begin{aligned} & 225 \\ & 5.25 \\ & 5.25 \\ & 5.25 \end{aligned}$ | $\begin{aligned} & \mathrm{V} \\ & \mathrm{~V} \\ & \mathrm{~V} \\ & \mathrm{~V} \end{aligned}$ |  |
| POWER SUPPLY CURRENTS ${ }^{3}$ <br> IVPP <br> All Channels at Full-Scale <br> All Channels at Zero-Scale <br> $I_{V+}$ <br> $I_{\text {AVCC }}$ <br> $I_{\text {DVCC }}$ |  | $\begin{aligned} & 80 \\ & 45 \\ & 0.75 \\ & 17.5 \\ & 0.25 \end{aligned}$ | $\begin{aligned} & 92 \\ & 55 \\ & 0.9 \\ & 20 \\ & 0.6 \end{aligned}$ | $\mu \mathrm{A} /$ channel <br> $\mu \mathrm{A} /$ channel <br> mA <br> mA <br> mA |  |

1 See the Terminology section.
${ }^{2}$ Linear output voltage range: 7 V to $\mathrm{V}_{\mathrm{PP}}-1.5 \mathrm{~V}$ or $51 \times$ REF_IN(whichever is less).
${ }^{3}$ Outputs unloaded.
${ }^{4}$ Ensure that maximum $T_{j}$ is not exceeded. See the Absolute Maximum Ratings section.
5 Output shorts to ground increase the on-chip power dissipation and therefore the chip junction temperature. Operation at or above the specified maximum operation junction temperature may impair device reliability.
${ }^{6}$ Reference input determines the output voltage range. The linear output voltage range is restricted from 7 V to $\mathrm{V}_{\mathrm{PP}}-1.5 \mathrm{~V}$, or $51 \times \mathrm{REF}$ _ N (whichever is less).

## SPECIFICATIONS

## TIMING CHARACTERISTICS

$\mathrm{V}_{\mathrm{PP}}=55 \mathrm{~V}$ to $225 \mathrm{~V} ; 4.75 \leq \mathrm{V}_{+} \leq 5.25 \mathrm{~V} ; 4.75 \mathrm{~V} \leq \mathrm{AV}_{\mathrm{CC}} \leq 5.25 \mathrm{~V} ; 2.7 \mathrm{~V} \leq \mathrm{DV} \mathrm{VCC} \leq 5.25 \mathrm{~V}$; PGND $=\mathrm{AGND}=\mathrm{DGND}=\mathrm{DAC}$ GND $=0 \mathrm{~V}$; $A V_{C C}$ and $V_{+}$must exceed REF_IN by 1.15 V minimum; $1 \mathrm{~V} \leq R E F \_\mathbb{N} \leq 4.096 \mathrm{~V} ;-10^{\circ} \mathrm{C} \leq \mathrm{T}_{\mathrm{A}} \leq+85^{\circ} \mathrm{C}$, unless otherwise noted.
Table 2. Timing Characteristics

| Parameter ${ }^{1,2,3}$ | Max | Min | Unit | Test Conditions/Comments |
| :---: | :---: | :---: | :---: | :---: |
| fupdate | 1.2 |  | MHz | Channel update rate |
| $\mathrm{f}_{\text {CLKIN }}$ | 30 |  | MHz | SCLK frequency |
| $\mathrm{t}_{1}$ |  | 13 | ns | SCLK high pulse width |
| $\mathrm{t}_{2}$ |  | 13 | ns | SCLK low pulse width |
| $t_{3}$ |  | 15 | ns | SYNC falling edge to SCLK falling edge setup time |
| $\mathrm{t}_{4}$ |  | 50 | ns | $\overline{\text { SYNC }}$ low time |
| $\mathrm{t}_{5}$ |  | 10 | ns | SYNC high time |
| $\mathrm{t}_{6}$ |  | 10 | ns | $\mathrm{D}_{\text {IN }}$ setup time |
| $\mathrm{t}_{7}$ |  | 5 | ns | $\mathrm{D}_{\text {IN }}$ hold time |
| $\mathrm{t}_{8}$ |  | 200 | ns | 19 ${ }^{\text {th }}$ SCLK falling edge to $\overline{\text { SYNC falling edge for next write }}$ |
| $\mathrm{t}_{9}$ |  | 20 | ns | $\overline{\text { RESET }}$ pulse width |

${ }^{1}$ See Figure 2.
${ }^{2}$ Guaranteed by design and characterization, not production tested.
${ }^{3}$ All input signals are specified with $\mathrm{tr}=\mathrm{tf}=5 \mathrm{~ns}\left(10 \%\right.$ to $90 \%$ of $\left.\mathrm{DV} \mathrm{CC}_{\mathrm{C}}\right)$ and timed from a voltage level of $\left(\mathrm{V}_{\mathrm{IL}}+\mathrm{V}_{\mathrm{IH}}\right) / 2$.


Figure 2. Serial Interface Timing Diagram

## ABSOLUTE MAXIMUM RATINGS

$T_{A}=25^{\circ} \mathrm{C}$, unless otherwise noted. Transient currents of up to 100 mA do not cause (silicon-controlled rectifier) SCR latch-up.
Table 3. Absolute Maximum Ratings

| Parameter | Rating |
| :---: | :---: |
| $\mathrm{V}_{\text {Pp }}$ to AGND | -0.3 V to +240 V |
| $V_{+}$to AGND | -0.3 V to +7 V |
| AV ${ }_{\text {CC }}$ to AGND, DAC_GND | -0.3 V to +7V |
| DV $\mathrm{cc}_{\text {c }}$ to DGND | -0.3 V to +7 V |
| Digital Inputs to DGND | $\begin{aligned} & -0.3 \mathrm{~V} \text { to } \mathrm{DV} \mathrm{CC}_{\mathrm{CC}}+0.3 \mathrm{~V} \text { or } \\ & +7 \mathrm{~V} \text { (whichever is less) } \end{aligned}$ |
| REF_IN to AGND, DAC_GND | $\begin{aligned} & -0.3 \mathrm{~V} \text { to } \mathrm{AV}_{\mathrm{CC}}+0.3 \mathrm{~V} \text { or }+7 \mathrm{~V} \\ & \text { (whichever is less) } \end{aligned}$ |
| $\mathrm{V}_{\text {OUTO }}$ to $\mathrm{V}_{\text {OUT }} 31$ to AGND | -0.3 V to V PP +0.3 V |
| ANODE/CATHODE to AGND, DAC_GND | -0.3 V to +7 V |
| AGND to DGND | -0.3 V to +0.3 V |
| Operating Temperature Range Industrial | $-10^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $-65^{\circ} \mathrm{C}$ to $+150^{\circ} \mathrm{C}$ |
| Junction Temperature (Maximum $\mathrm{T}_{\mathrm{J}}$ ) | $150^{\circ} \mathrm{C}$ |
| Lead Temperature | JEDEC industry standard |
| Soldering | J-STD-020 |

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

## THERMAL RESISTANCE

Thermal performance is directly linked to printed circuit board (PCB) design and operating environment. Careful attention to PCB thermal design is required.
$\theta_{\mathrm{JA}}$ is the natural convection junction-to-ambient thermal resistance measured in a one cubic foot sealed enclosure.

Table 4. Thermal Resistance

| Package Type | $\theta_{\mathrm{JA}}$ | Unit |
| :--- | :--- | :--- |
| BC-124-4 | 40 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

## ELECTROSTATIC DISCHARGE (ESD) RATINGS

The following ESD information is provided for handling of ESD-sensitive devices in and ESD-protected area only.

Human body model (HBM) per ANSI/ESDA/JEDEC JS-001.
Field induced charged-device model (FICDM) per ANSI/ESDA/JEDEC JS-002.

ESD Ratings for the AD45335
Table 5. AD45335, 124-Lead CSP_BGA

| ESD Model | Withstand Threshold (V) | Class |
| :--- | :--- | :--- |
| HBM | 2500 | 2 |
| FICDM | 400 | C1 |

ESD CAUTION

|  | ESD (electrostatic discharge) sensitive device. Charged devi- <br> ces and circuit boards can discharge without detection. Although <br> this product features patented or proprietary protection circuitry, <br> damage may occur on devices subjected to high energy ESD. <br> Therefore, proper ESD precautions should be taken to avoid <br> performance degradation or loss of functionality. |
| :---: | :---: |

## PIN CONFIGURATION AND FUNCTION DESCRIPTIONS



Figure 3. Pin Configuration
Table 6. Pin Function Descriptions

| Pin No. | Mnemonic | Description |
| :---: | :---: | :---: |
| A1 | NC | No Connect. Do not connect to these pins. |
| A2 | $\mathrm{V}_{\text {OUT }}{ }^{1}$ | Analog Output Voltages from the 32 Channels. |
| A4 | $\mathrm{V}_{\text {OUT }} 7$ | Analog Output Voltages from the 32 Channels. |
| A6 | $\mathrm{V}_{\text {Out }} 11$ | Analog Output Voltages from the 32 Channels. |
| A8 | Vout16 | Analog Output Voltages from the 32 Channels. |
| A10 | $\mathrm{V}_{\text {OUT } 20}$ | Analog Output Voltages from the 32 Channels. |
| A12 | $\mathrm{V}_{\text {OUT } 25}$ | Analog Output Voltages from the 32 Channels. |
| A14 | NC | No Connect. Do not connect to these pins. |
| B1 | $\mathrm{V}_{\text {OUT }} 0$ | Analog Output Voltages from the 32 Channels. |
| B3 | $\mathrm{V}_{\text {OUT }} 4$ | Analog Output Voltages from the 32 Channels. |
| B5 | $\mathrm{V}_{\text {OUT }} 9$ | Analog Output Voltages from the 32 Channels. |
| B7 | $\mathrm{V}_{\text {OUT }} 13$ | Analog Output Voltages from the 32 Channels. |
| B9 | Vout 17 | Analog Output Voltages from the 32 Channels. |
| B11 | $\mathrm{V}_{\text {OUT }} 21$ | Analog Output Voltages from the 32 Channels. |
| B13 | $\mathrm{V}_{\text {OUT } 26}$ | Analog Output Voltages from the 32 Channels. |
| C2 | $\mathrm{V}_{\text {Out }}{ }^{3}$ | Analog Output Voltages from the 32 Channels. |
| C12 | $\mathrm{V}_{\text {OUT } 22}$ | Analog Output Voltages from the 32 Channels. |
| C14 | $\mathrm{V}_{\text {OUT }} 29$ | Analog Output Voltages from the 32 Channels. |
| D1 | $\mathrm{V}_{\text {Out }}{ }^{2}$ | Analog Output Voltages from the 32 Channels. |
| D13 | $\mathrm{V}_{\text {OUT }} 23$ | Analog Output Voltages from the 32 Channels. |
| E2 | $V_{\text {OuT }} 5$ | Analog Output Voltages from the 32 Channels. |
| E4 | $\mathrm{V}_{\text {OUT }} 8$ | Analog Output Voltages from the 32 Channels. |
| E6 | $\mathrm{V}_{\text {OUT }} 12$ | Analog Output Voltages from the 32 Channels. |
| E8 | Vout15 | Analog Output Voltages from the 32 Channels. |
| E10 | $\mathrm{V}_{\text {Out }} 19$ | Analog Output Voltages from the 32 Channels. |
| E12 | $\mathrm{V}_{\text {OUT } 24}$ | Analog Output Voltages from the 32 Channels. |
| E14 | $\mathrm{V}_{\text {OUT }} 31$ | Analog Output Voltages from the 32 Channels. |
| F3 | $\mathrm{V}_{\text {Out }} 6$ | Analog Output Voltages from the 32 Channels. |
| F5 | $\mathrm{V}_{\text {Out }} 10$ | Analog Output Voltages from the 32 Channels. |
| F7 | $\mathrm{V}_{\text {OUT }} 14$ | Analog Output Voltages from the 32 Channels. |
| F9 | $\mathrm{V}_{\text {Out }} 18$ | Analog Output Voltages from the 32 Channels. |
| F13 | Vout30 | Analog Output Voltages from the 32 Channels. |
| G14 | $\mathrm{V}_{\text {OUT } 28}$ | Analog Output Voltages from the 32 Channels. |
| H1, H2 | $V_{\text {PP }}$ | Output Amplifier High Voltage Supply. |
| H4 to H11 | AGND | Analog GND Pins. |
| H13 | $\mathrm{V}_{\text {OUT }} 27$ | Analog Output Voltages from the 32 Channels. |
| J3 to J12 | AGND | Analog GND Pins. |

## PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

Table 6. Pin Function Descriptions (Continued)

| Pin No. | Mnemonic | Description |
| :---: | :---: | :---: |
| K1, K2 | $V_{+}$ | $V_{+}$Amplifier Supply Pins. |
| K3 to K14 | AGND | Analog GND Pins. |
| L1, L2 | NC | No Connect. Do not connect to these pins. |
| L3 to L13 | AGND | Analog GND Pins. |
| L14 | DAC_GND | Reference GND Supply for All DACs. |
| M1 to M12 | AGND | Analog GND Pins. |
| M13, M14 | $\mathrm{AV}_{\text {cC }}$ | Analog Supply Pins. |
| N1, N2 | PGND | Output Amplifier Ground Reference Pins. |
| N3 | CATHODE | Cathode of Internal Diode for Diode Temperature Measurement. |
| N4 | ANODE | Anode of Internal Diode for Diode Temperature Measurement. |
| N5 to N14 | AGND | Analog GND Pins. |
| P1 | NC | No Connect. Do not connect to these pins. |
| P2 | REF_IN | Reference Voltage for Channel 0 to Channel 31. |
| P3 | DAC_GND | Reference GND Supply for All DACs. |
| P4 | RESET | Active Low Input. This pin can also be used to reset the complete device to its power-on reset conditions. Zero code is loaded to the DACs. |
| P5 | DV ${ }_{\text {cc }}$ | Digital Supply Pins. |
| P6 | DGND | Digital GND Pins. |
| P7 | TEST | For normal operation, tie this pin low. |
| P8 | $\mathrm{D}_{\mathrm{IN}}$ | Serial Data Input. Data must be valid upon the falling edge of SCLK. |
| P9 | SCLK | Serial Clock Input. Data is clocked into the shift register upon the falling edge of SCLK. The pin operates at clock speeds of up to 30 MHz . Internal pull-up device on logic input. Therefore, it can be left floating and defaults to a logic high condition. |
| P10 | SYNC | Active Low Input. This is the frame synchronization signal for the serial interface. While $\overline{\text { SYNC }}$ is low, data is transferred in upon the falling edge of SCLK. |
| P11 to P13 | AGND | Analog GND Pins. |
| P14 | NC | No Connect. Do not connect to these pins. |

## TYPICAL PERFORMANCE CHARACTERISTICS



Figure 4. INL with Full-Scale Range $=50 \mathrm{~V}$


Figure 5. DNL with Full-Scale Range $=50 \mathrm{~V}$


Figure 6. INL with Full-Scale Range $=200 \mathrm{~V}$


Figure 7. DNL with Full-Scale Range $=200 \mathrm{~V}$


Figure 8. Short-Circuit Current Limit Timing


Figure 9. Worst-Case Adjacent Channel Crosstalk

## TYPICAL PERFORMANCE CHARACTERISTICS



Figure 10. Output Amplifier Source and Sink Capability


Figure 11. Offset Error vs. Temperature


Figure 12. Gain Error vs. Temperature


Figure 13. Cumulative DC Crosstalk Effects on a Single-Channel Output, Switching All Other Channels in Sequence


Figure 14. Settling Time Rising Edge at Various Capacitive Loads


Figure 15. Settling Time Falling Edge at Various Capacitive Loads

## TERMINOLOGY

## Integral Nonlinearity (INL)

A measure of the maximum deviation from a straight line passing through the endpoints of the DAC transfer function. It is expressed as a percentage of full-scale range.

## Differential Nonlinearity (DNL)

The difference between the measured change and the ideal 1 LSB change between any two adjacent codes. A specified DNL of $\pm 1$ LSB maximum ensures monotonicity.

## Zero Code Voltage

A measure of the output voltage present at the device output with all 0 s loaded to the DAC. It includes the offset of the DAC and the output amplifier and is expressed in V .

## Offset Error

Calculated by taking two points in the linear region of the transfer function, drawing a line through these points, and extrapolating back to the $y$-axis. It is expressed in V .

## Voltage Gain

Calculated from the change in output voltage for a change in code, multiplied by 16,384 , and divided by the REF_IN voltage. This is calculated between two points in the linear section of the transfer function.

## Gain Error

A measure of the output error with all 1s loaded to the DAC, and the difference between the ideal and actual analog output range. Ideally, the output should be $50 \times$ REF_IN. It is expressed as a percentage of full-scale range.

## DC Power Supply Rejection Ratio (PSRR)

A measure of the change in analog output for a change in $V_{P P}$ supply voltage. It is expressed in dB , and $\mathrm{V}_{\mathrm{Pp}}$ is varied $\pm 5 \%$.

## DC Crosstalk

The DC change in the output level of one DAC at midscale in response to a full-scale code change (all 0 s to all 1 is and vice versa) and the output change of all other DACs. It is expressed in LSB.

## Output Voltage Settling Time

The time taken from when the last data bit is clocked into the DAC until the output has settled to within $\pm 0.5 \mathrm{LSB}$ of its final value. Measured for a step change of $1 / 4$ to $3 / 4$ full scale.

## Digital-to-Analog Glitch Impulse

The area of the glitch injected into the analog output when the code in the DAC register changes state. It is specified as the area of the glitch in nV -sec when the digital code is changed by 1 LSB at the major carry transition ( $011 \ldots 11$ to $100 \ldots 00$ or $100 \ldots 00$ to $011 \ldots$ 11).

## Analog Crosstalk

The area of the glitch transferred to the output $\left(V_{\text {OUT }}\right)$ of one DAC due to a full-scale change in the output ( $V_{\text {OUT }}$ ) of another DAC. The area of the glitch is expressed in nV -sec.

## Digital Feedthrough

A measure of the impulse injected into the analog outputs from the digital control inputs when the part is not being written to (SYNC is high). It is specified in nV -sec and measured with a worst-case change on the digital input pins, for example, from all 0 s to all 1 s and vice versa.

## Output Noise Spectral Density

A measure of internally generated random noise. Random noise is characterized as a spectral density (voltage per VHz ). It is measured by loading all DACs to midscale and measuring noise at the output. It is measured in $\mu \mathrm{V} / \mathrm{VHz}$.

## THEORY OF OPERATION

The AD45335 consists of a 32-channel, 14-bit DAC with 200 V high voltage amplifiers in a single $15 \mathrm{~mm} \times 15 \mathrm{~mm}$ chip scale package ball grid array (CSP_BGA). The output voltage range is programmable through the $\operatorname{RE} \bar{E} \_\mathbb{N}$ pin. The output range is 0 V to 50 V when REF_IN $=1 \mathrm{~V}$, and $0-\mathrm{V}$ to 200 V when REF_IN $=4 \mathrm{~V}$. Communication to the device is through a serial interface operating at clock rates of up to 30 MHz , which is compatible with digital signal processing (DSP) and microcontroller interface standards. A 5 -bit address and a 14-bit data-word are loaded into the AD45335 input register through the serial interface. The channel address is decoded, and the data-word is converted into an analog output voltage for this channel.

At power-on, all the DAC registers are loaded with 0 s.

## DAC SECTION

The architecture of each DAC channel consists of a resistor string DAC, followed by an output buffer amplifier operating with a nominal gain of 50 . The voltage at the REF_IN pin provides the reference voltage for the corresponding DAC. The input coding to the DAC is straight binary, and the ideal DAC output voltage is given by
$V_{\text {OUT }}=\frac{50 \times V_{\text {REF IN }} \times D}{2^{14}}$
where $D$ is the decimal equivalent ( 0 to 16,383 ) of the binary code, which is loaded to the DAC register.
The output buffer amplifier is specified to drive a load of $4 \mathrm{M} \Omega$ and 200 pF . The linear output voltage range for the output amplifier is from 7 V to $\mathrm{V}_{\mathrm{PP}}-1.5 \mathrm{~V}$. The amplifier output bandwidth is typically 30 kHz , and is capable of sourcing $150 \mu \mathrm{~A}$ and sinking $40 \mu \mathrm{~A}$.

## RESET FUNCTION

The reset function on the AD45335 can be used to reset all nodes on the device to their power-on reset condition. All the DACs are loaded with 0s, and all registers are cleared. Take the RESET pin low to implement the reset function.

## SERIAL INTERFACE

The serial interface is controlled by the following pins:

- $\overline{\text { SYNC, }}$, which is the frame synchronization pin for the serial interface.
- SCLK, which is the serial clock input that operates at clock speeds of up to 30 MHz .
- $D_{\text {IN }}$, which is the serial data input, and data must be valid upon the falling edge of SCLK.
To update a single DAC channel, a 19-bit data-word is written to the AD45335 input register, as shown in Figure 16.


## A4 to A0 Bits

The A4 to A0 bits can address any one of the 32 channels. A4 is the MSB of the address, while A0 is the LSB.

## DB13 to DB0 Bits

The DB13 to DB0 bits are used to write a 14-bit data-word into the addressed DAC register.
Figure 2 is the timing diagram for a serial write to the AD45335. The serial interface works with both a continuous and a discontinuous serial clock. The first falling edge of SYNC resets the serial clock counter to ensure that the correct number of bits are shifted into the serial shift register. Any further edges on SYNC are ignored until the correct number of bits are shifted in. After 19 bits are shifted in, the SCLK is ignored. For another serial transfer to take place, the counter must be reset by the falling edge of SYNC. The user must allow 200 ns (minimum) between successive writes.


Figure 16. Serial Data Format

## APPLICATIONS INFORMATION

## MEMS MIRROR CONTROL APPLICATION

The AD45335 is targeted to all optical switching control systems based on MEMS technology. The AD45335 is a 32-channel, 14-bit DAC with integrated high voltage amplifiers. The output amplifiers are capable of generating an output range of 0 V to 200 V when using a 4 V reference. The full-scale output voltage is programmable from 50 V to 200 V using reference voltages from 1 V to 4 V . Each amplifier can output $150 \mu \mathrm{~A}$ sourcing current and directly drives the control actuators, which determine the position of MEMS mirrors in optical switch applications.

The AD45335 is generally used in a closed-loop feedback system, as shown in Figure 17, with a high resolution analog-to-digital converter (ADC) and DSP. The exact position of each mirror is measured using capacitive sensors. The sensor outputs are multiplexed using an ADG739 4-to-1 multiplexer (MUX) to an 8-channel, 14-bit ADC (AD7856). An alternative solution is to multiplex using a 32-to-1 multiplexer (ADG732) into a single-channel ADC (AD7671). With 14-bit monotonic behavior and a 0 V to 200 V output range, coupled with its fast serial interface, the AD45335 is ideally suited for controlling a cluster of MEMS-based mirrors.


Figure 17. AD45335 in a MEMS-Based Optical Switch

## APPLICATIONS INFORMATION

## IPC-221-COMPLIANT BOARD LAYOUT

The diagram in Figure 18 is a typical 2 -layer PCB layout for the AD45335 that complies with the specifications outlined in IPC-221. Do not connect to the four corner balls labeled as original no connects. Connect balls labeled as additional no connects to AGND.

The routing shown in Figure 18 shows the feasibility of connecting to the high voltage balls while complying with the spacing requirements of IPC-221. Figure 18 also shows the physical distances that are available.


Figure 18. Layout Guidelines to Comply with IPC-221

## APPLICATIONS INFORMATION

## POWER SUPPLY DECOUPLING RECOMMENDATIONS

On the AD45335, it is recommended to tie all grounds together as close to the device as possible. If the number of supplies must be reduced, bring all supplies back separately and make a provision on the PCB through a link option to drive the $A V_{c c}$ and $V_{+}$pins from the same supply. Decouple all power supplies adequately with 10 $\mu \mathrm{F}$ tantalum capacitors and $0.1 \mu \mathrm{~F}$ ceramic capacitors.

## GUIDELINES FOR PCB LAYOUT

Design PCBs such that the analog and digital sections are separated and confined to the designated analog and digital sections of the board. This facilitates the use of ground planes that can be separated easily. A minimum etch technique is generally the best for ground planes because it optimizes shielding of sensitive signal lines. Join digital and analog ground planes in one place only, at the AGND and DGND pins of the high resolution converter. To isolate the high frequency bus of the processor from the bus of the high resolution converters, buffer or latch data and address buses on the board. These act as a Faraday shield and increase the signal-to-noise performance of the converters by reducing the amount of high frequency digital coupling. Avoid running digital lines under the device because they couple noise onto the die. Allow the ground plane to run under the IC to avoid noise coupling.
Use as large a trace as possible for the supply lines of the device to provide low impedance paths and reduce the effects of glitches on the power supply line. Shield components, such as clocks with fast-switching signals, with digital ground to avoid radiating noise to other sections of the board. Never run clock signals near the analog inputs of the device. Avoid crossovers of digital and analog signals.

Keep traces for analog inputs as wide and short as possible and shield with analog ground if possible. Run traces on opposite sides of the 2-layer PCB at right angles to each other to reduce the effects of feedthrough through the board.
A microstrip technique is by far the best, but it is not always possible to use with a double-sided board. In this technique, the component side of the board is dedicated to ground planes, and signals are placed on the solder side. Multilayer PCBs with dedicated ground, power, and tracking layers offer the optimum solution in terms of obtaining analog performance, but at increased manufacturing costs.

Good decoupling is vitally important when using high resolution converters. Decouple all analog supplies with $10 \mu \mathrm{~F}$ tantalum capacitors in parallel with $0.1 \mu \mathrm{~F}$ ceramic capacitors to analog ground. To achieve the best results from the decoupling components, place them as close to the device as possible, ideally right up against the IC or the IC socket. The main aim of a bypassing element is to maximize the charge stored in the bypass loop while simultaneously minimizing the inductance of this loop. Inductance in the loop acts as an impedance to high frequency transients and results in power supply spiking. By keeping the decoupling as close to the device as possible, the loop area is kept as small as possible, thereby reducing the possibility of power supply spikes. Decouple digital supplies of high resolution converters with $10 \mu \mathrm{~F}$ tantalum capacitors and $0.1 \mu \mathrm{~F}$ ceramic capacitors to the digital ground plane. Decouple the $\mathrm{V}_{+}$supply with a $10 \mu \mathrm{~F}$ tantalum capacitor and a $0.1 \mu \mathrm{~F}$ ceramic capacitor to AGND.

Decouple all logic chips with $0.1 \mu \mathrm{~F}$ ceramic capacitors to digital ground to decouple high frequency effects associated with digital circuitry.

## OUTLINE DIMENSIONS



Figure 19. 124-Lead Chip Scale Package Ball Grid Array [CSP_BGA]
(BC-124-4)
Dimensions shown in millimeters

## ORDERING GUIDE

| Model $^{1}$ | Temperature Range | Package Description | Package Option |
| :--- | :--- | :--- | :--- |
| AD45335KBCZ | $-10^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | 124 -Ball CSP-BGA $(15 \mathrm{~mm} \times 15 \mathrm{~mm} \times 1.29 \mathrm{~mm})$ | BC-124-4 |
| ${ }^{1} \mathrm{Z}=$ RoHS Compliant Part. |  |  |  |

## EVALUATION BOARD

| Model $^{1}$ | Description |
| :--- | :--- |
| EVAL-AD45335SDZ | AD45335 Evaluation Board |
| 1 Z $=$ RoHS Compliant Part. |  |

